

<b>INFORMATION DISCLOSURE CITATION #3</b> PTO-1449 APR 25 2002 U.S. PATENT & TRADEMARK OFFICE	Atty. Docket No. 020200	Serial No. 10/084,367
	Applicant(s): Ryota Nanjo et al	
	Filing Date: February 28, 2002	Group Art Unit: <sup>3833</sup> Not Yet Assigned

### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
JMJ	AA	5,956,603	Talwar et al	9/21/99	438	520
	AB					

### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
JMJ	AF 2001-007220	1/12/01	JP	Yes, abstract
	AG 2000-269491	9/29/00	JP	Yes, abstract
	AH 2000-196037	7/14/00	JP	Yes, abstract
	AI 07-231044	8/29/95	JP	Yes, abstract
	AJ 06-053157	2/25/94	JP	Yes, abstract
JMJ	AK 05-067776	3/19/93	JP	Yes, abstract

### OTHER DOCUMENTS

JMJ	AL	"Activation and Deactivation of Laser Thermal Annealed Boron, Arsenic, Phosphorus and Antimony Ultra-Shallow Abrupt Junctions", Murto et al; TH-13; Ion Implantation Technology 2000
JMJ	AM	"Self-Aligned Nickel-Mono-Silicide Technology for High-Speed Deep Submicrometer Logic CMOS USI", Morimoto et al; Vol 42, No. 5, May 1995 IEEE, pp 915-923.
JMJ	AN	"70nm MOSFET with Ultra-shallow, Abrupt, and Super-doped S/D extension Implemented by Laser Thermal Process (LTP); Bin Yu et al; 1999 IEEE
JMJ	AO	"Front End Processes"; International Technology Roadmap for Semiconductors 1999; pp 105-141
Examiner	JMJ	Date Considered 10-30-03

RECEIVED  
APR 25 2002  
2833  
MAIL ROOM